

General Purpose Transistors

PNP, 65 V, 100 mA

NST856MTWFT

The NST856MTWFT is designed for general purpose amplifier applications. It is housed in an ultra-compact DFN1010-3 with wettable flanks, recommended for the automotive industry's optical inspection methods. The transistor is ideal for low-power surface mount applications where board space and reliability are at a premium.

Features

- Wettable Flank Package for Optimal Automated Optical Inspection (AOI)
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

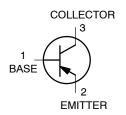
Rating	Symbol	Max	Unit
Collector - Emitter Voltage	V_{CEO}	-65	Vdc
Collector - Base Voltage	V_{CBO}	-80	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	Ic	-100	mA
Collector Current - Peak	I _{CM}	200	mA

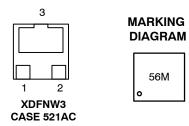
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	191	°C/W
Total Power Dissipation per Device @T _A = 25°C (Note 1)	P _D	650	mW
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

1. Per JESD51-7 with standard PCB footprint and 2 oz. Cu.





56 = Specific Device Code
M = Month Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST856MTWFTBG	XDFNW3 (Pb-Free)	3000 / Tape & Reel
NSVT856MTWFTBG	XDFNW3 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = −10 mA)	V _{(BR)CEO}	-65	-	-	V
Collector – Emitter Breakdown Voltage (I _C = -10 μA, V _{EB} = 0)	V _{(BR)CES}	-80	_	_	V
Collector – Base Breakdown Voltage (I _C = -10 μA)	V _{(BR)CBO}	-80	-	-	V
Emitter – Base Breakdown Voltage ($I_E = -0.1 \mu A, I_C = 0$)	V _{(BR)EBO}	-5.0	-	_	V
Collector Cutoff Current $(V_{CB} = -30 \text{ V})$ $(V_{CB} = -30 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}	- -	- -	-15.0 -5.0	nΑ μΑ
Emitter – Base Cutoff Current (V _{BE} = -6 V, I _C = 0)	I _{EBO}	-	-	-0.1	μΑ
ON CHARACTERISTICS					
DC Current Gain (Note 2) $ \begin{pmatrix} I_C = -10 \ \mu\text{A}, \ V_{CE} = -5.0 \ \text{V}) \\ (I_C = -2.0 \ \text{mA}, \ V_{CE} = -5.0 \ \text{V}) \end{pmatrix} $	h _{FE}	- 220	150 290	- 450	
Collector – Emitter Saturation Voltage (Note 2) (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{CE(sat)}	- -	- -	-0.25 -0.60	V
Base – Emitter Saturation Voltage (Note 2) (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	-	-0.7 -0.9	-	V
Base – Emitter Turn–on Voltage (Note 2) $ (I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V}) $ $ (I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V}) $	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Transition Frequency ($I_C = -10$ mA, $V_{CE} = -5.0$ V, $f = 100$ MHz)	f _T	100	-	_	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, f = 1.0 \text{ MHz})$	C _{obo}	-	1.8	4.0	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	1.0	-	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Pulse Condition: Pulse Width = 300 $\mu s,$ Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

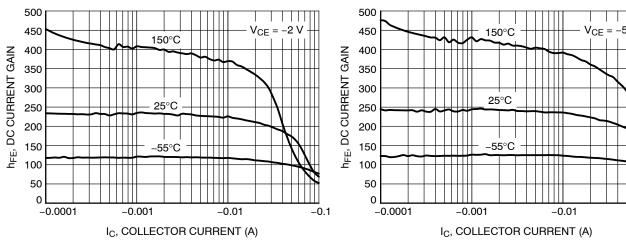


Figure 1. DC Current Gain

Figure 2. DC Current Gain

-0.1

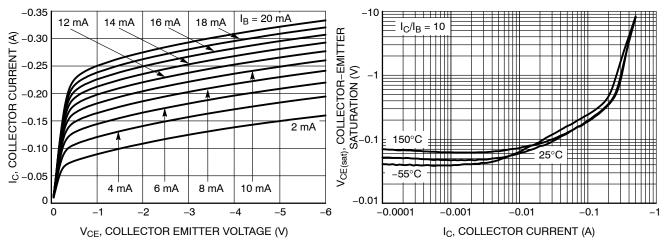


Figure 3. Collector Current as a Function of Collector Emitter Voltage

Figure 4. Collector-Emitter Saturation Voltage

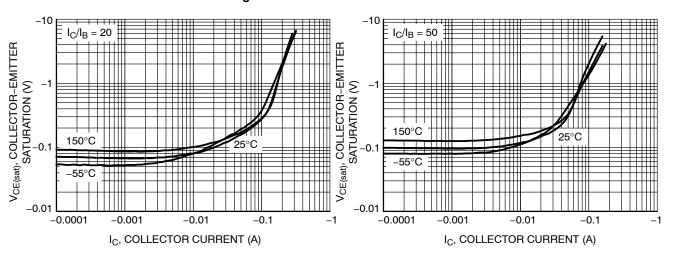
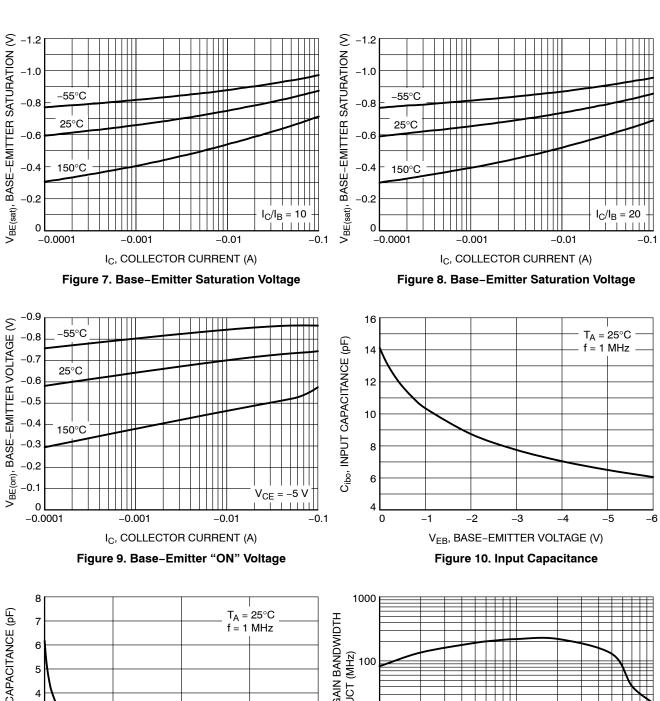


Figure 5. Collector-Emitter Saturation Voltage

Figure 6. Collector-Emitter Saturation Voltage

TYPICAL CHARACTERISTICS



Cobo, OUTPUT CAPACITANCE (pF) f_T, CURRENT GAIN BANDWIDTH PRODUCT (MHz) 3 2 $T_J = 25^{\circ}C$ V_{CE} = −2 V 1 f_{test} = 100 MHz 0 0 -20 -40 -10 -100 V_{CB}, COLLECTOR-BASE REVERSE VOLTAGE (V) I_C, COLLECTOR CURRENT (mA)

Figure 11. Output Capacitance

Figure 12. f_T, Current Gain Bandwidth Product

TYPICAL CHARACTERISTICS

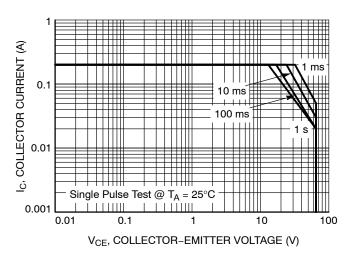


Figure 13. Safe Operating Area

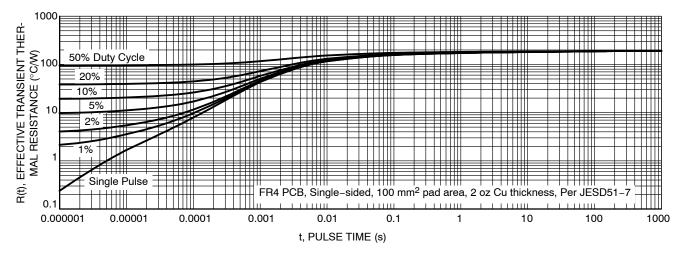


Figure 14. Thermal Resistance

PIN 1 REFERENCE



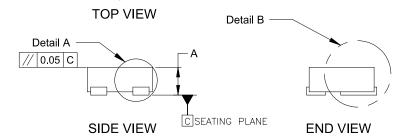
XDFNW3 1.00x1.00x0.38 0.65P CASE 521AC ISSUE B

DATE 07 MAY 2024

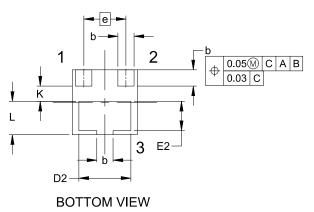
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
Α	0.32	0.38	0.44
A1	0.00		0.04
А3	0.125 REF		
b	0.20	0.25	0.30
D	0.90	1.00	1.10
D1	0.00		0.04
D2	0.75	0.80	0.85
Е	0.90	1.00	1.10
E2	0.40	0.45	0.50
е		0.65 BSC	
L	0.465	0.515	0.565
K		0.23 REF	



В

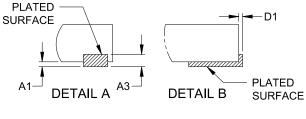


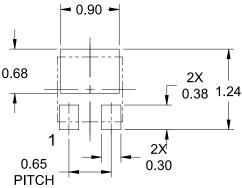




XX = Specific Device CodeM = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.





RECOMMENDED MOUNTING FOOTPRINT*

 For additional information on our Pb-Free strategy and soldering details, please download the ONSEMI Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	Thinked versions are uncontrolled except when stamped CONTROLLED O		
I DESCRIPTION: I	XDFNW3 1.00x1.00x0.38 0.65P		PAGE 1 OF 1

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